Efficient Radical-Based NIR Organic Light-Emitting Diodes with

Emission peak Exceeding 800 nm

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General information

All reagents and solvents required for synthesis and characterization are purchased from commercial suppliers and used directly without any treatment. The nuclear magnetic resonance (¹H NMR) spectra were recorded on the Bruker AVANCEIII 500 spectrometer at 500 MHz at 298 K and tetramethyl silane (TMS) ($\delta H = 0$ ppm) as the internal standard. MALDI-TOF mass spectra were recorded on a Brucker Autoflex speed TOF/TOF mass spectrometer with DCTB as a matrix. A shimadzu UV-2550 spectrophotometer was applied to record the ultraviolet (UV)-visible spectra. Fluorescence spectra were recorded using a RF-5301 PC spectrophotometer and QE pro. All of PLQEs are determined with a calibrated integrating sphere system and using QE pro of Ocean Insight as fluorescence spectrometer. The electrochemical oxidation and reduction potentials were recorded using an electrochemical analyzer (CHI660C, CH Instruments, USA). The fluorescence decay spectra were recorded on an Edinburgh fluorescence spectrometer (FLS980), and the lifetime of the excited states was measured by the time-correlated single photon counting method under the excitation of a laser (378 nm). Elemental analysis (C, H and N) was performed on a Elementar Vario micro cube elemental analyzer. Thermal gravimetric analysis (TGA) was characterized by a TAINSTRUMENTS Q500 TGA analyzer. Ready-made indium tin oxide (ITO) glass substrates were purchased and cleaned. After dried with N2, they were treated with UV irradiation for 20 min and next transferred to a vacuum deposition system with the pressure of $1-4 \times 10^{-6}$ mbar. The MoO₃ layer was deposited at a rate of 0.1 Å s⁻¹. All the organic layers were deposited at 0.2-0.4 Å s⁻¹. The evaporation rate of cathode LiF

and Al metal layer were 0.1 Å s⁻¹ and 0.3-0.8 Å s⁻¹ respectively. The current-voltage characteristics were measured using a Keithley 2400 programmable electrometer. The EL spectra and EQEs were measured using QE pro spectroradiometer of Ocean Insight together with a calibrated integrating sphere at room temperature in glove box.

1. Synthesis Section

The HTTM was prepared as reported¹.



Scheme S1. The synthesis route of TTM-NPNA

(1) Synthesis of HTTM-PA

HTTM (1.00 g, 1.80 mmol) and 4-(4,4,5,5-tetramethyl-1,3,2-dioxaborolan-2-yl) - aniline (0.39 g, 1.80 mmol) was dissolved in a mixed solvent of toluene (12 ml), K_3PO_4 aqueous solution (8 ml, 2 mol / L) and ethanol (4 ml), and catalyst Pd(PPh₃)₄ (0.10 g, 0.09 mmol) was added under argon atmosphere. The mixture was stirred at 95°C for 48

h under argon atmosphere. After the reaction mixture cooling to room temperature, the solution was extracted with dichloromethane. Organic layer was collected and dried. The solvent was removed under vacuum and the crude product was purified by silica gel column chromatography (using petroleum ether: dichloromethane = 8:1 v/v). **HTTM-PA** was obtained as a white solid (0.39 g, 36% yield). ¹H NMR (500 MHz, CD_2Cl_2) δ 7.54 (d, J = 2.0 Hz, 1H), 7.41 (s, 2H), 7.41 – 7.40 (m, 2H), 7.39 (s, 1H), 7.29 – 7.25 (m, 2H), 6.76 (s, 1H), 6.75 (d, J = 3.7 Hz, 2H), 4.08 (s, 2H). MALDI-TOF-MS (m/z): calculated for C₂₅H₁₃Cl₈N, 608.853; found, 608.664. Elem. Anal. Calcd for C₂₅H₁₃Cl₈N: C 49.15, H 2.14, N 2.29; found, C 50.11, H 2.43, N 2.29.

(2) Preparation of HTTM-NPNA

HTTM-PA (1.22 g, 2.00 mmol) and 2-bromonaphthalene (1.24 g, 6.00 mmol) was dissolved in dry toluene (25 ml). Pt(t-Bu)₃ (0.62 ml, 10%w/v, 0.30 mmol), Cs₂CO₃ (1.95 g, 6.00 mmol) and catalyst Pd(OAc)₂ (33.70 mg, 0.15 mmol) was added under argon atmosphere. The mixture was stirred at 115°C for 48 h under argon atmosphere. After the reaction mixture cooling to room temperature, the solution was extracted with dichloromethane. Organic layer was collected and dried. The solvent was removed under vacuum and the crude product was purified by silica gel column chromatography (using petroleum ether: dichloromethane = 10:1 v/v). **HTTM-NPNA** was obtained as a white solid (1.02 g, 59% yield). ¹H NMR (500 MHz, CD₂Cl₂) δ 7.84 (s, 1H), 7.82 (d, J = 2.7 Hz, 2H), 7.81 (d, J = 2.4 Hz, 1H), 7.66 (d, J = 2.1 Hz, 1H), 7.65 (s, 1H), 7.54 (s, 2H), 7.44 (d, J = 1.9 Hz, 1H), 7.43 (s, 2H), 7.42 (d, J = 2.1 Hz, 2H), 7.38 (d, J = 2.2 Hz, 1H), 7.34 (d, J = 2.2 Hz, 1H), 7.32 (d, J = 2.2 Hz, 2H), 7.24 (d, J = 2.2 Hz, 1H), 7.07

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(d, J = 2.4 Hz, 1H), 6.93 (d, J = 2.4 Hz, 1H), 6.71 (s, 1H). MALDI-TOF-MS (m/z): calculated for $C_{45}H_{25}Cl_8N$, 862.944; found, 862.063. Elem. Anal. Calcd for $C_{45}H_{25}Cl_8N$: C 62.61, H 2.92, N 1.62; found, C 62.65, H 2.80, N 1.63.

(3) Preparation of **TTM-NPNA**

Under argon atmosphere and in the dark, **HTTM-NPNA** (0.86 g, 1.00 mmol) was dissolved in dry THF (20 ml). Then t-BuOK (1.12 g, 10.00 mmol) was added. The solution was stirred for 5 h in the dark at room temperature, and then p-Chloranil (1.23 g, 5.00 mmol) was added. The solution was stirred for further 1 h. After the reaction finished, the solvent was removed under vacuum and the crude product was purified by silica gel column chromatography (using petroleum ether: dichloromethane = 10:1 v/v). The crude product was recrystallized twice from dichloromethane and methanol and a gray solid was obtained (0.65 g, 75% yield). MALDI-TOF-MS (m/z): calculated for C₄₅H₂₄Cl₈N, 861.936; found, 861.064. Elem. Anal. Calcd for C₄₅H₂₄Cl₈N: C 62.68, H 2.81, N 1.62; found, C 62.80, H 2.92, N 1.58.



Fig. S1 ¹H-NMR spectrum of HTTM-PA in CD₂Cl₂.



Fig. S2 ¹H-NMR spectrum of HTTM-NPNA in CD₂Cl₂.



Fig. S3 MALDI-TOF-MS spectrum of HTTM-PA.



Fig. S4 MALDI-TOF-MS spectrum of HTTM-NPNA.



Fig. S5 MALDI-TOF-MS spectrum of TTM-NPNA.

2.Photophysical Parameters of TTM-NPNA in different solvents



Fig. S6 The normalized UV-vis absorption and PL spectra of **TTM-NPNA** in various solvents (10⁻⁵ M) at room temperature.



Fig. S7 Fluorescence decay curves of TTM-NPNA in (a) toluene and (b) n-butyl ether.

Radical	Solvent	$\lambda_{abs}^{[a]}$ (nm)	λ _{PL} [b][c] (nm)	PLQE ^{[b][c]} (%)	τ ^[d] (ns)	${k_r^{CT[e]}} \ 10^7 \ ({s^{-1}})$	k _{nr} ^{CT[e]} 10 ⁷ (s ⁻¹)
	cyclohexane	655	745	23	6.7	3.41	11.42
TTM-	toluene	671	810	24	7.3	3.27	10.36
NPNA	n-butyl ether	665	818	16	5.3	3.01	15.82
	chloroform	669	916	1	_[f]	-	-

Table S1. Photophysical parameters of TTM-NPNA in different solvents.

^[a] long-wavelength absorption in different solvents. ^[b] excited at 375nm. ^[c] measured with a calibrated integrating sphere system. ^[d] measured using Edinburgh fluorescence spectrometer (FLS980) at room temperature. ^[e] Calculated from the equation: $\phi = k_r/(k_r + k_{nr})$; $\tau = 1/(k_r + k_{nr})$. ^[f] beyond the measurement-range of the instruments.



Fig. S8 The optimized geometry configuration of D_0 state and the related dihedral angles (θ_1 , θ_2 and θ_3) for **TTM-NPNA** in cyclohexane.

TTM-		$ heta_1(\circ)$			$ heta_2(^\circ)$			$ heta_3(\circ)$	
NPNA	D_0	D_1	$\Delta_{D_1-D_0}$	D_0	D_1	$\Delta_{D_1-D_0}$	D	D D1	$\Delta_{D^{1}-D^{0}}$
cyclohexane	29.9	35.9	6.0	-34.8	-53.2	-18.4	-44	.4 -35.0	9.4
toluene	29.8	35.2	5.4	-34.7	-51.9	-17.2	-44	.5 -35.3	9.2
chloroform	29.4	32.6	3.2	-34.2	-47.9	-13.7	-44	.9 -36.4	8.5

Table S2. The dihedral angle values of θ_1 - θ_3 and their variations between D₀ and D₁ states.

3. TGA curve and Electrochemical properties



Fig. S9 TGA thermograph of **TTM-NPNA** recorded under nitrogen at a heating rate of 10°C/min.



Fig. S10. Repeated cyclic voltammetry measurements (15 cycles) of TTM-NPNA.

4. Extracted results of TD-DFT calculations

TTM-NPNA (UB3LYP/6-31G(d,p))

Excitation energies and oscillator strengths:

Excited State 1: 2.091-A 1.5810 eV 784.20 nm f=0.1332 <S**2>=0.843 218B ->219B 0.98617 This state for optimization and/or second-order correction. Total Energy, E(TD-HF/TD-KS) = -5465.52635848 Copying the excited state density for this state as the 1-particle RhoCI density.

Excited State	2:	2.305-A	2.4508 eV	505.89 nm	f=0.0056
<s**2>=1.078</s**2>					
218A ->220)A	-0.16112			
219A ->220)A	0.29581			
209B ->219	θB	0.11975			
215B ->219	θB	-0.44792			
217B ->219)B	0.74203			
218B ->219)B	0.14752			
218B ->220)B	-0.16418			
Excited State	3:	3.438-A	2.4711 eV	501.73 nm	f=0.0000
<s**2>=2.706</s**2>					
216A ->220)A	0.11739			
216A ->224	1A	0.25205			
217A ->221	ΙA	-0.22416			
218A ->221	IA	-0.22240			
219A ->221	IA	-0.52468			
219A ->227	7A	-0.10348			
216B ->219)B	-0.16451			
216B ->220)B	-0.13409			
216B ->223	BB	-0.24739			
217B ->221	В	0.24547			
218B ->221	В	0.54130			
Excited State	4:	3.322-A	2.5607 eV	484.19 nm	f=0.0493
<s**2>=2.509</s**2>					
216A ->221	ΙA	-0.29310			
217A ->224	1A	0.17737			
218A ->224	1A	0.14744			
219A ->220)A	0.47508			

219A ->224A	0.27358			
219A ->228A	0.10079			
216B ->221B	0.29601			
217B ->219B	-0.30468			
217B ->223B	-0.19798			
218B ->220B	-0.40712			
218B ->223B	-0.26063			
Excited State 5:	2.188-A	2.6616 eV	465.82 nm	f=0.0090
<s**2>=0.947</s**2>				
218A ->222A	-0.23673			
219A ->222A	0.14212			
210B ->219B	0.14490			
212B ->219B	0.44213			
213B ->219B	0.54713			
214B ->219B	-0.51927			
216B ->219B	-0.26230			
Excited State 6:	2.117 - A	2.6638 eV	465.44 nm	f=0.0018
<s**2>=0.871</s**2>				
212B ->219B	0.11840			
213B ->219B	0.14405			
214B ->219B	-0.15543			
216B ->219B	0.94935			
218B ->221B	0.11242			
Excited State 7:	2.301-A	2.7531 eV	450.34 nm	f=0.0195
<s**2>=1.074</s**2>				
216A ->221A	-0.11334			
218A ->220A	0.25456			
219A ->220A	-0.17118			
219A ->224A	0.14007			
209B ->219B	-0.24370			
211B ->219B	-0.19640			
215B ->219B	0.57833			
216B ->221B	0.11402			
217B ->219B	0.57497			
218B ->223B	-0.12426			
				_
Excited State 8:	2.154-A	2.7921 eV	444.05 nm	f=0.0075
<s**2>=0.910</s**2>				
218A ->222A	-0.21466			
219A ->222A	0.14175			
210B ->219B	0.16996			

212B ->219B	0.70755			
213B ->219B	-0.38094			
214B ->219B	0.44804			
Excited State 9:	2.970-A	2.8506 eV	434.93 nm	f=0.1757
<s**2>=1.955</s**2>				
215A ->220A	0.10446			
216A ->221A	0.24002			
217A ->220A	-0.16295			
217A ->224A	-0.15571			
218A ->220A	-0.12064			
219A ->220A	0.48242			
219A ->224A	-0.20922			
219A ->228A	0.12138			
209B ->219B	-0.18184			
211B ->219B	-0.35909			
215B ->219B	0.34148			
215B ->220B	-0.11281			
216B ->221B	-0.23546			
217B ->220B	0.17787			
217B ->223B	0.14267			
218B ->220B	-0.13720			
218B ->223B	0.24333			
Excited State 10:	2.111-A	2.9776 eV	416.39 nm	f=0.0038
<s**2>=0.864</s**2>				
218A ->222A	-0.11999			
218A ->223A	0.14382			
210B ->219B	0.90067			
212B ->219B	-0.31915			
Excited State 11:	2.268-A	2.9836 eV	415.56 nm	f=0.0115
<s**2>=1.036</s**2>				
218A ->220A	0.13846			
218A ->225A	0.10267			
209B ->219B	-0.41835			
211B ->219B	0.81426			
218B ->220B	-0.12859			
Excited State 12.	2.287-A	3.0839 eV	402 04 nm	f=0.1136
< <u>S**2>=1.057</u>	, , , , , , , , , , , , , , , , , ,	2.000000		
212A ->72A	0 13613			
2121 ->2221 218A ->220A	-0 14279			
2184 ->2201	0 14701			
21011 - 22011	0.17/71			

-0.12648			
0.24898			
0.12445			
0.45049			
0.48817			
0.26632			
-0.10652			
0.40018			
0.11268			
0.13171			
2.469-A	3.1356 eV	395.41 nm	f=0.6507
-0.10543			
-0.30671			
0.11401			
0.35587			
-0.21053			
-0.30319			
0.12790			
-0.11150			
0.69524			
0.69524			
0.69524 -0.12173			
0.69524 -0.12173 2.894-A	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646	3.2048 eV	386.87 nm	f=0.0217
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646 2.731-A	3.2048 eV 3.2572 eV	386.87 nm 380.65 nm	f=0.0217 f=0.0279
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646 2.731-A	3.2048 eV 3.2572 eV	386.87 nm 380.65 nm	f=0.0217 f=0.0279
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646 2.731-A -0.16668	3.2048 eV 3.2572 eV	386.87 nm 380.65 nm	f=0.0217 f=0.0279
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646 2.731-A -0.16668 0.20422	3.2048 eV 3.2572 eV	386.87 nm 380.65 nm	f=0.0217 f=0.0279
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646 2.731-A -0.16668 0.20422 0.24924	3.2048 eV 3.2572 eV	386.87 nm 380.65 nm	f=0.0217 f=0.0279
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646 2.731-A -0.16668 0.20422 0.24924 0.11243	3.2048 eV 3.2572 eV	386.87 nm 380.65 nm	f=0.0217 f=0.0279
0.69524 -0.12173 2.894-A 0.11294 0.21049 -0.31180 0.76182 0.10176 -0.16421 -0.19787 0.25372 0.14646 2.731-A -0.16668 0.20422 0.24924 0.11243 0.17949	3.2048 eV 3.2572 eV	386.87 nm 380.65 nm	f=0.0217 f=0.0279
	-0.12648 0.24898 0.12445 0.45049 0.48817 0.26632 -0.10652 0.40018 0.11268 0.13171 2.469-A -0.10543 -0.30671 0.11401 0.35587 -0.21053 -0.30319 0.12790 -0.11150	-0.12648 0.24898 0.12445 0.45049 0.48817 0.26632 -0.10652 0.40018 0.11268 0.13171 2.469-A 3.1356 eV -0.10543 -0.30671 0.11401 0.35587 -0.21053 -0.30319 0.12790 -0.11150	-0.12648 0.24898 0.12445 0.45049 0.48817 0.26632 -0.10652 0.40018 0.11268 0.13171 2.469-A 3.1356 eV 395.41 nm -0.10543 -0.30671 0.11401 0.35587 -0.21053 -0.30319 0.12790 -0.11150

218B ->221B	0.78069			
218B ->226B	0.13456			
218B ->227B	0.10227			
Excited State 16:	2.236-A	3.2636 eV	379.90 nm	f=0.1915
<s**2>=1.000</s**2>				
218A ->222A	-0.54070			
219A ->222A	0.61709			
210B ->219B	-0.27206			
212B ->219B	-0.35738			
213B ->219B	-0.12547			
218B ->221B	0.11944			
Excited State 17: <pre><s**2>=0.849</s**2></pre>	2.096-A	3.2993 eV	375.79 nm	f=0.0007
208B ->219B	-0.23315			
213B ->219B	0.67844			
214B ->219B	0.67843			
Excited State 18:	2.532-A	3.3728 eV	367.60 nm	f=0.0338
<s**2>=1.353</s**2>				
216A ->221A	0.16670			
217A ->224A	-0.12189			
218A ->220A	0.62369			
219A ->220A	0.33763			
219A ->224A	0.33325			
215B ->219B	-0.22610			
216B ->221B	-0.13436			
217B ->223B	0.15872			
218B ->220B	0.32236			
218B ->223B	-0.10950			
Excited State 19:	3.223-A	3.4075 eV	363.86 nm	f=0.0011
<s**2>=2.347</s**2>				
214A ->221A	0.11050			
216A ->221A	0.20603			
217A ->224A	-0.22973			
218A ->220A	-0.38489			
218A ->224A	0.10066			
219A ->220A	-0.10652			
219A ->224A	0.51359			
219A ->228A	-0.15923			
216B ->221B	-0.20786			
217B ->223B	0.19834			

218B ->220B	-0.16868			
218B ->223B	-0.43265			
218B ->228B	-0.10084			
Excited State 20:	2.383-A	3.4570 eV	358.64 nm	f=0.0087
<s**2>=1.169</s**2>				
218A ->223A	-0.56986			
219A ->223A	0.72656			
219A ->226A	-0.19102			
210B ->219B	0.15469			
218B ->226B	0.11843			

5.Electroluminescence Performances



Fig. S11 Electroluminescent properties of **TTM-NPNA**. (a) Materials used in this work; (b) PL spectrum of the **TTM-NPNA** doped film (5.0 wt%-doped in CBP film); (c) EL spectra of **TTM- NPNA** from 4.5-11V; (d) The curve of current density versus EQE for **TTM-NPNA** based device.



Fig. S12 Summary of EQE in state-of-the-art NIR-OLEDs against the EL peak wavelength (over 800 nm).



Fig. S13 Measured angular dependence of electroluminescence of **TTM-NPNA** based OLED with the dopant concentration of 5 wt% (black squares), and the angular dependence predicted for Lambertian emission (red dotted line).



Fig. S14 Variation of (a) EL intensity and (b) spectra of the **TTM-NPNA** based device versus operating time driven at a constant current density of 6 mA/cm².

λELmax	EQE	Emitter material	[ref]	λELmax	FOF (%)	Emitter material	[ref]
(nm)	(%)		[iei]	(nm)			lieij
800	1.9	metal free emitter	2	800	1	metal complex emitter	3
802	0.43	metal free emitter	4	803	9.58	metal complex emitter	5
804	2.2	metal free emitter	6	811	0.97	metal complex emitter	7
810	0.51	metal free emitter	8	814	1.5	metal complex emitter	9
814	0.5	metal free emitter	10	826	0.49	metal complex emitter	11
822	3.9	metal free emitter	This work	847	0.19	metal complex emitter	13
823	0.27	metal free emitter	12	848	2.8	metal complex emitter	15
824	0.16	metal free emitter	14	846	1.5	metal complex emitter	15
828	0.41	metal free emitter	8	855	1	metal complex emitter	17
830	2.47	metal free emitter	16	890	3.8	metal complex emitter	18
830	3.1	metal free emitter	35	900	3.8	metal complex emitter	20
838	0.58	metal free emitter	19	920	1.9	metal complex emitter	22
840	1.12	metal free emitter	21	1005	0.2	metal complex emitter	20
840	3.8	metal free emitter	23	1060	0.022	metal complex emitter	24
850	0.14	metal free emitter	12	1060	0.3	metal complex emitter	25
852	0.3	metal free emitter	8				
864	0.2	metal free emitter	4	1			
868	0.09	metal free emitter	12	1			
870	0.02	metal free emitter	12	1			
883	0.1	metal free emitter	26	1			

Table S3. Summary of the device performances of NIR-OLEDs published to date with maximum electroluminescent (EL) wavelength over 800 nm.

890	0.015	metal free emitter	27
894	0.23	metal free emitter	8
895	0.091	metal free emitter	28
901	1.1	metal free emitter	29
904	0.019	metal free emitter	30
905	1.32	metal free emitter	31
916	0.07	metal free emitter	19
939	0.006	metal free emitter	28
960	0.009	metal free emitter	26
990	0.018	metal free emitter	28
1010	0.003	metal free emitter	32
1050	0.05	metal free emitter	33
1050	0.16	metal free emitter	34
1050	0.33	metal free emitter	34
1080	0.73	metal free emitter	34

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